

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW96** is Designed for High Linearity Class A, AB HF Power Amplifier Applications up to 30 MHz.

FEATURES:

- $P_E = 14$ dB Typical at 200 W/28 MHz
- $IMD_3 = -32$ dBc Typ. at 220 W(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	12 A
V_{EES}	110 V
V_{CEO}	55 V
V_{EBO}	4.0 V
P_{DISS}	320 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$0.7^\circ C/W$

PACKAGE STYLE .500 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		.125 / 3.18
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E		.125 / 3.18
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

ORDER CODE: ASI10826

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 50$ mA	110			V
BV_{CEO}	$I_C = 200$ mA	55			V
BV_{EBO}	$I_E = 20$ mA	4.0			V
I_{CES}	$V_{CE} = 55$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 7.0$ A	15		50	---
V_{CE}	$I_C = 20$ A $I_C = 4.0$ A			1.9	V
C_C	$V_{CB} = 50$ V $f = 1.0$ MHz		280		pF
G_P	$V_{CE} = 50$ V $I_{CQ} = 100$ mA $P_{OUT} = 200$ W(PEP)	13.5		-30	dB
IMD_3					dBc
η_C		40			%